

SPTECH Silicon PNP Power Transistor

MJ15012

DESCRIPTION

- Excellent Safe Operating Area
- DC Current Gain-
: $h_{FE} = 20(\text{Min.}) @ I_C = -2A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -2.5V(\text{Max}) @ I_C = -4A$
- Complement to the NPN MJ15011

APPLICATIONS

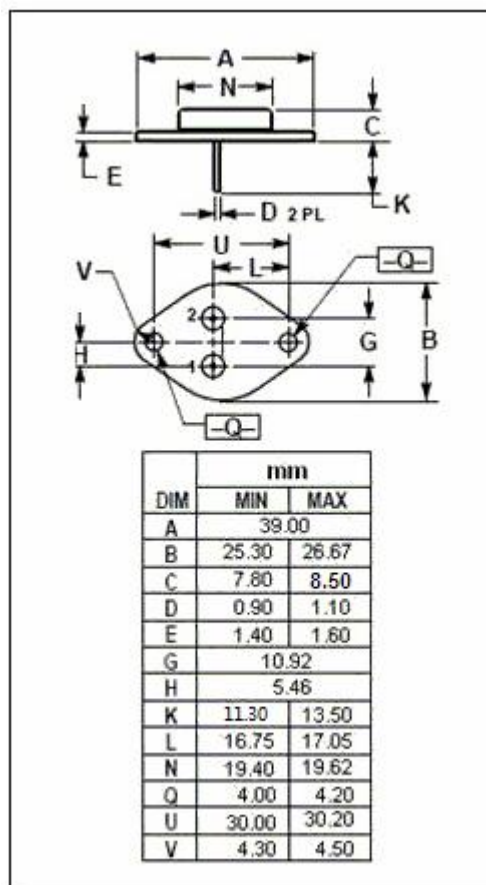
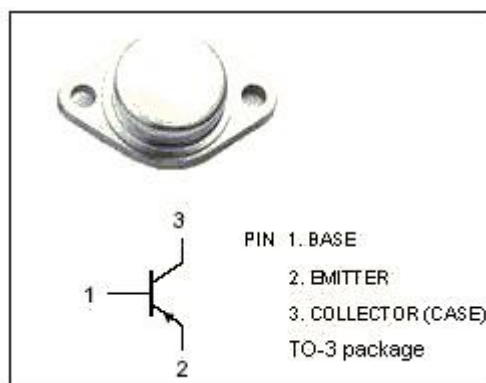
- Designed for high power audio, disk head positioners , and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, DC-DC converters or inverters.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Voltage	-250	V
V_{CEX}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
I_B	Base Current-Continuous	-2	A
I_{BM}	Base Current-Peak	-5	A
I_E	Emitter Current-Continuous	12	A
I_{EM}	Emitter Current-Peak	20	A
P_D	Total Power Dissipation@ $T_c=25^{\circ}\text{C}$	200	W
T_j	Junction Temperature	200	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65~200	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.875	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -50mA ; I _B = 0	-250		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A		-0.8	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A		-2.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -4A ; V _{CE} = -2V		-2.0	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -200V; I _B = 0		-1.0	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = -250V; I _E =0		-0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0		-0.5	mA
h _{FE-1}	DC Current Gain	I _C = -2A ; V _{CE} = -2V	20	100	
h _{FE-2}	DC Current Gain	I _C = -4A ; V _{CE} = -2V	5		
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = -10V; f _{test} = 1.0MHz	500		pF